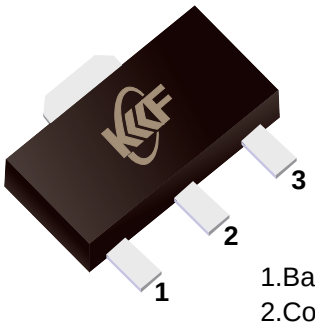
2SD882

NPN Transistors



1.Base
2.Collector
3.Emitter

Simplified outline(SOT-89)

Features

- NPN transistor High current output up to 3A
- Low Saturation Voltage
- Complement to 2SB772

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	40	V
Collector to Emitter Voltage	V_{CEO}	30	V
Emitter to Base Voltage	V_{EBO}	6	V
Collector Current to Continuous	I_C	3	A
Collector Dissipation	P_C	0.5	W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{stg}	-55 to 150	℃

Electrical Characteristics Ta = 25℃

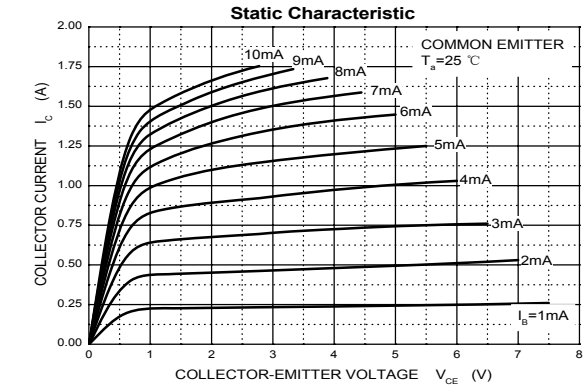
Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V_{CBO}	I_C=100uA ,I_E=0	40			V
Collector-emitter breakdown voltage	V_{CEO}	I_C= 10 mA , I_B=0	30			V
Emitter-base breakdown voltage	V_{EBO}	I_E= 100 uA ,I_C=0	6			V
Collector cut-off current	I_{CBO}	V_{CB}=40 V , I_E=0			1	uA
Collector cut-off current	I_{CEO}	V_{CE}=30 V , I_B=0			10	uA
Emitter cut-off current	I_{EBO}	V_{EB}=6V , I_C=0			1	uA
DC current gain	h_{FE}	V_{CE}= 2V, I_C= 1A	60		400	
		V_{CE}=2V, I_C= 100mA	32			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=2A, I_B= 0.2A			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C=2A, I_B= 0.2A			1.5	V
Transition frequency	f_T	V_{CE}=5 V, I_C=0.1mA,f = 10MHz	50			MHz

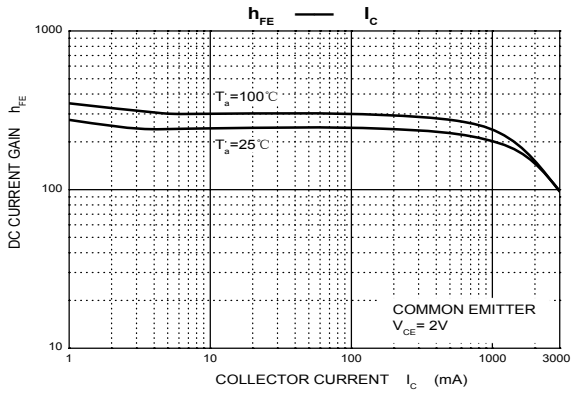
Classification of $h_{fe(1)}$

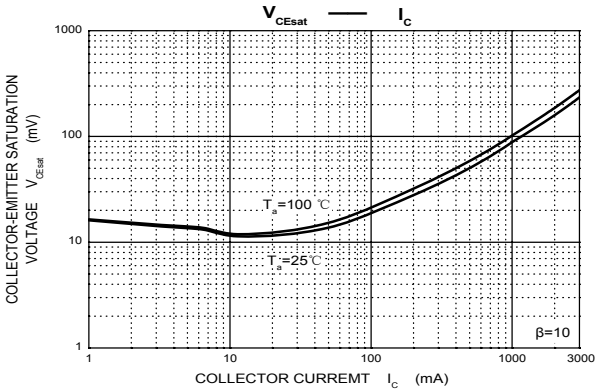
Type	2SD882-R	2SD882-Q	2SD882-P	2SD882-E
Range	60-120	100-200	160-320	200-400

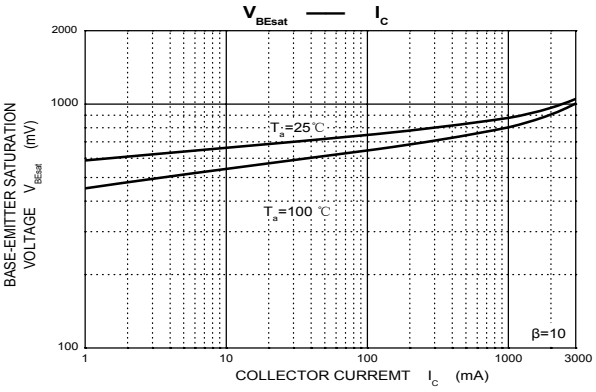
2SD882

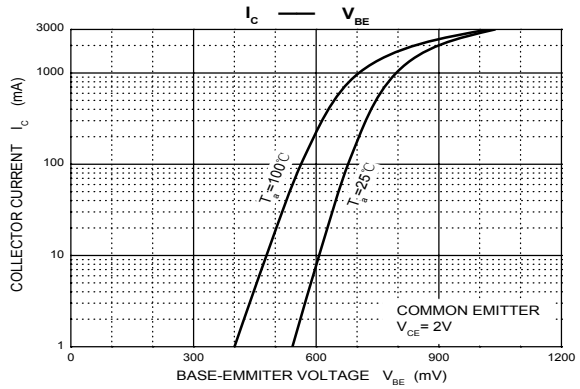
■ Typical Characterisitics

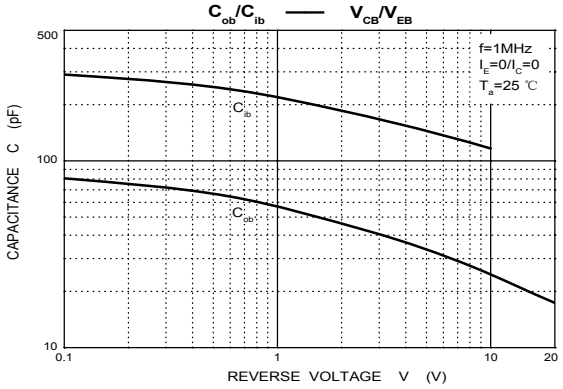


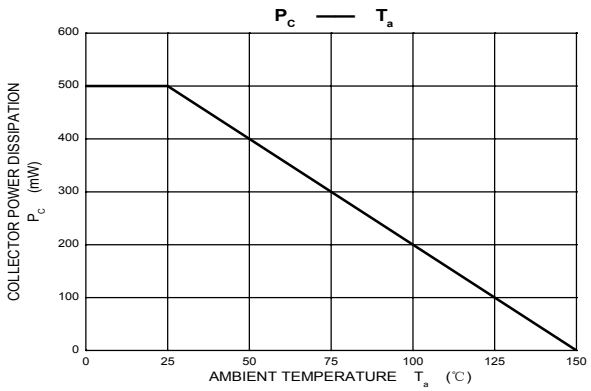












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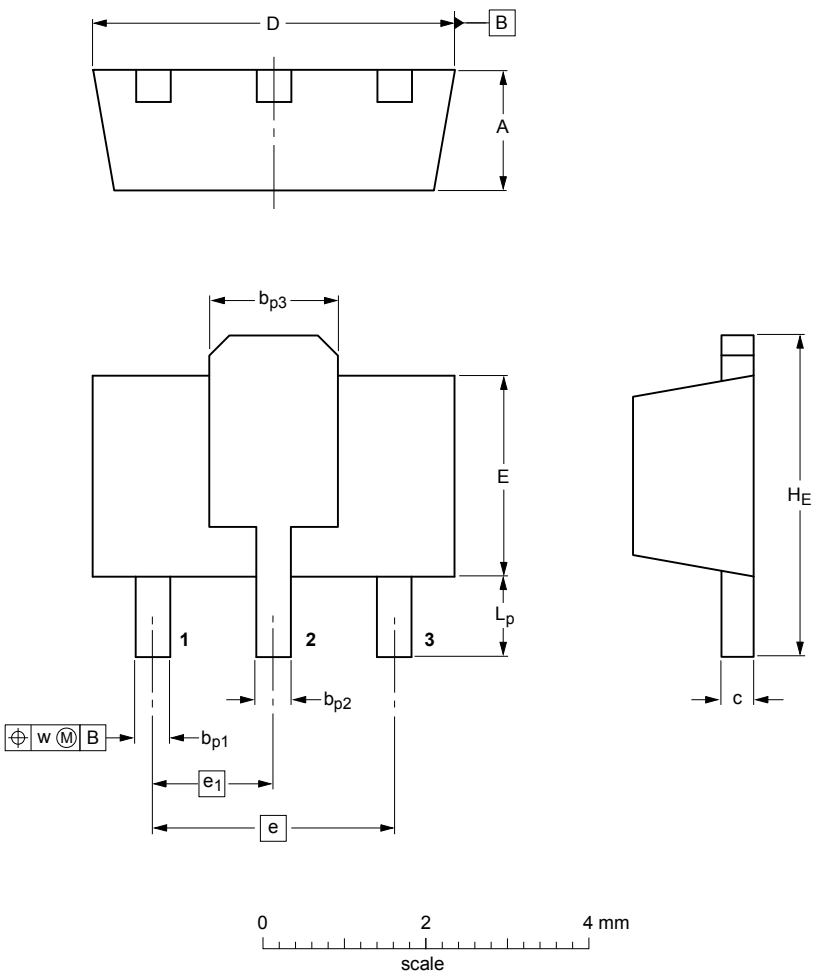
■ SOT-89



DIMENSIONS (mm are the original dimensions)

UNIT	A	b_{p1}	b_{p2}	b_{p3}	c	D	E	e	e_1	H_E	L_p	w
mm	1.6 1.4	0.48 0.35	0.53 0.40	1.8 1.4	0.44 0.23	4.6 4.4	2.6 2.4	3.0	1.5	4.25 3.75	1.2 0.8	0.13